

**1. Material** Substrate GaAs (N Type)  
Epitaxial Layer GaAlAs (P/N Type)

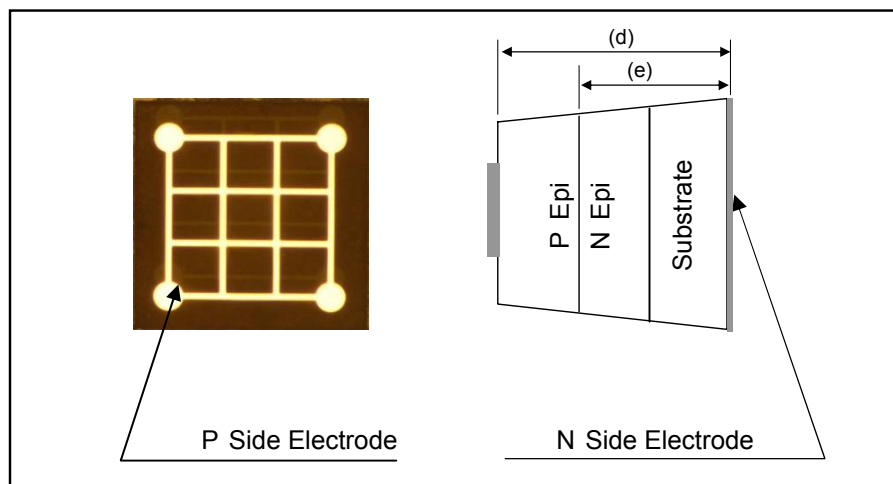
**2. Electrode** N(Cathode) Side Gold Alloy  
P(Anode) Side Gold Alloy

**3. Electro-Optical Characteristics**

Parameter	Symbo	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_F$			1.35	V	IF=250mA
Reverse Voltage	$V_R$	5			V	IR=10uA
Radiant Power	$P_O$		8.5		mW	IF=250mA
Wavelength	$\lambda_P$		940		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : LED Chip is mounted on TO-18 gold header without resin coating.

**4. Mechanical Data** (a) Emission Area ----- 38.5mil x 38.5mil  
 (b) Bottom Area ----- 40.0mil x 40.0mil  
 (c) Bonding Pad ----- 120um  
 (d) Chip Thickness ----- 11mil  
 (e) Junction Height ----- 6.7mil



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